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# 2SA1484

Silicon PNP Epitaxial

# HITACHI

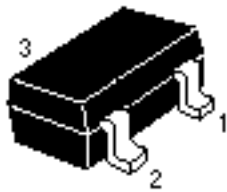
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## Application

Low frequency amplifier

## Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

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## 2SA1484

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### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-90	V
Collector to emitter voltage	$V_{CEO}$	-90	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

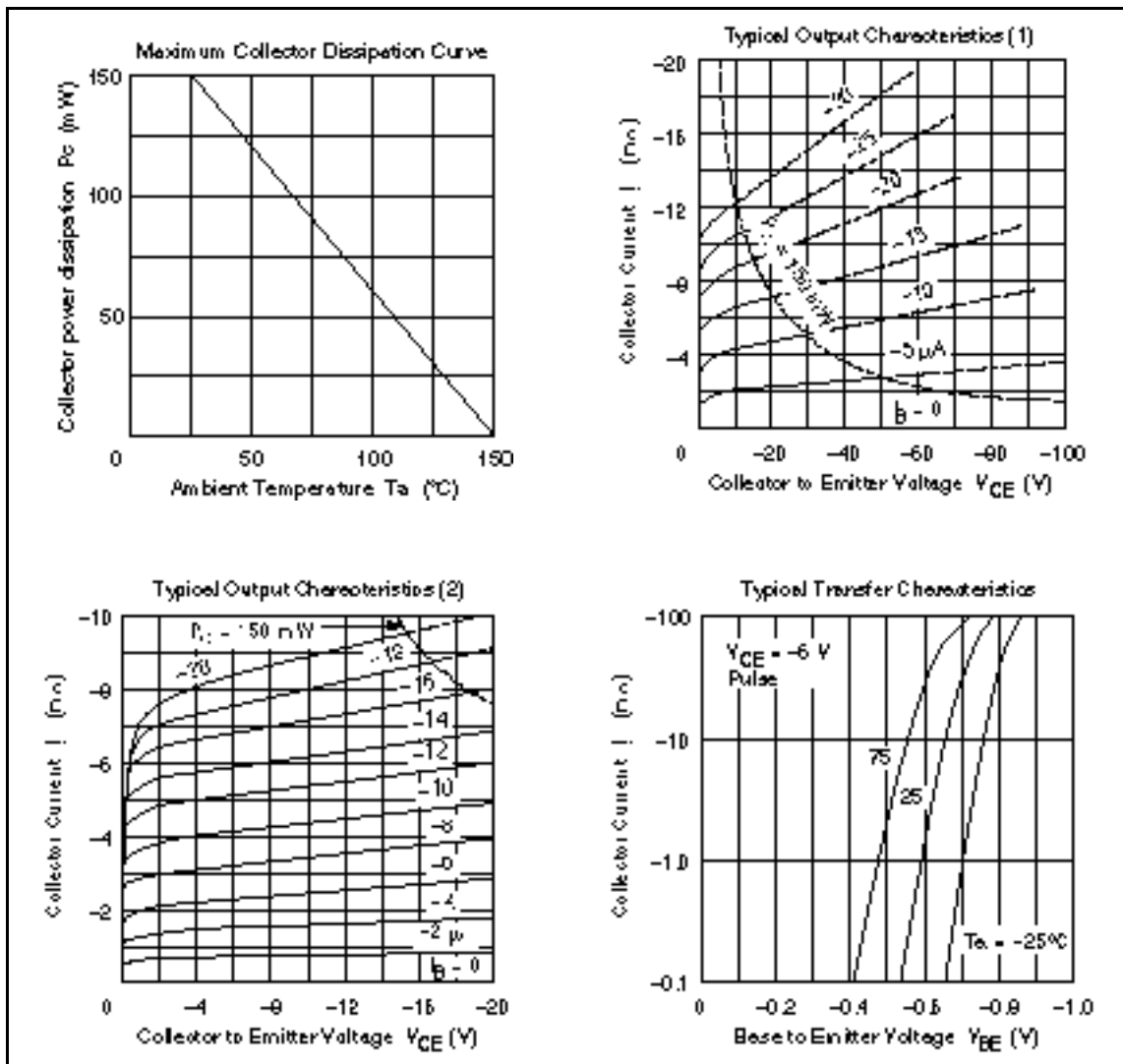
### Electrical Characteristics (Ta = 25°C)

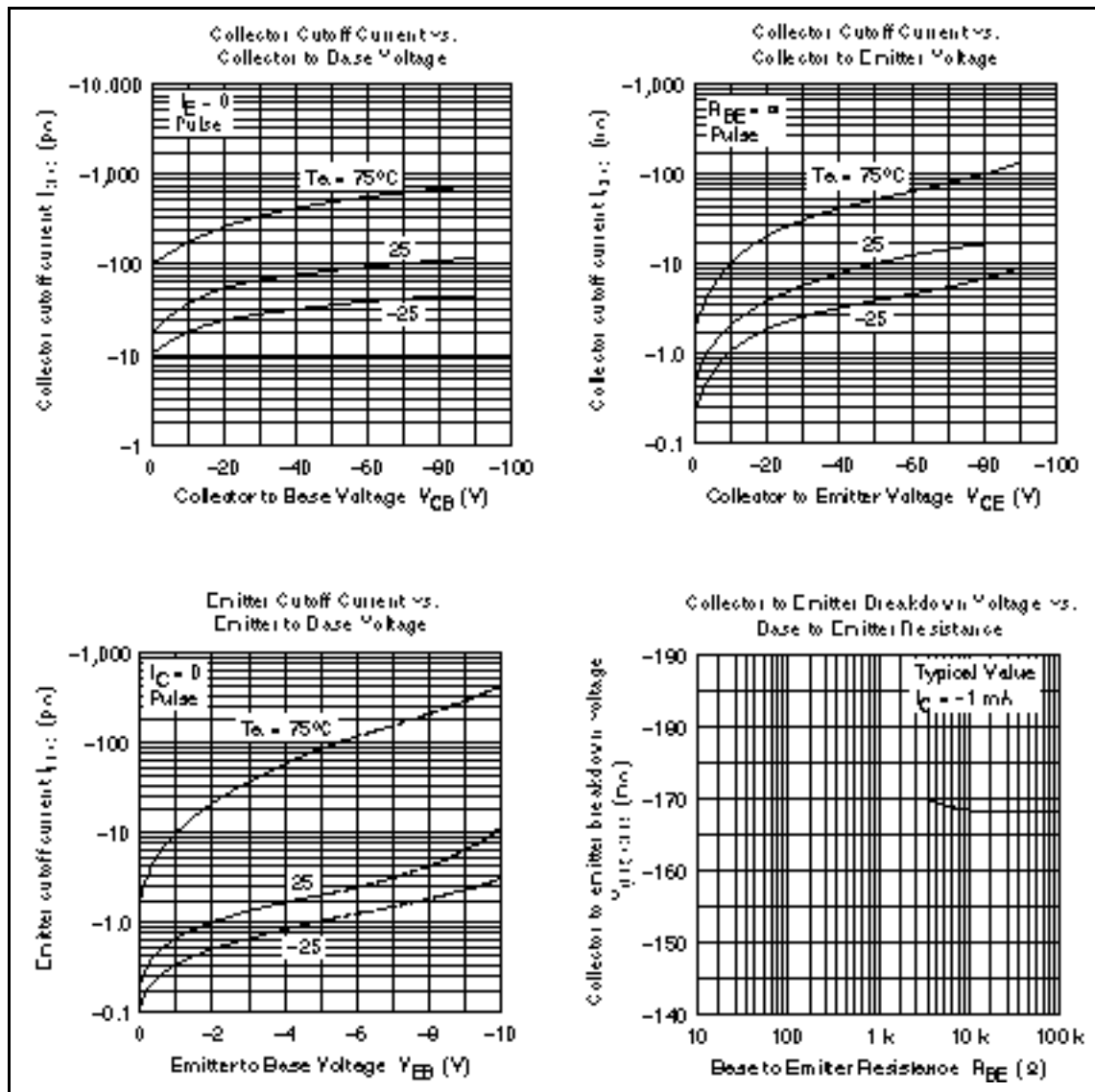
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	—	—	V	$I_C = -1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-0.1	$\mu A$	$V_{CB} = -70 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	-0.1	$\mu A$	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	250	—	800		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.15	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	-1.0	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}^{*2}$

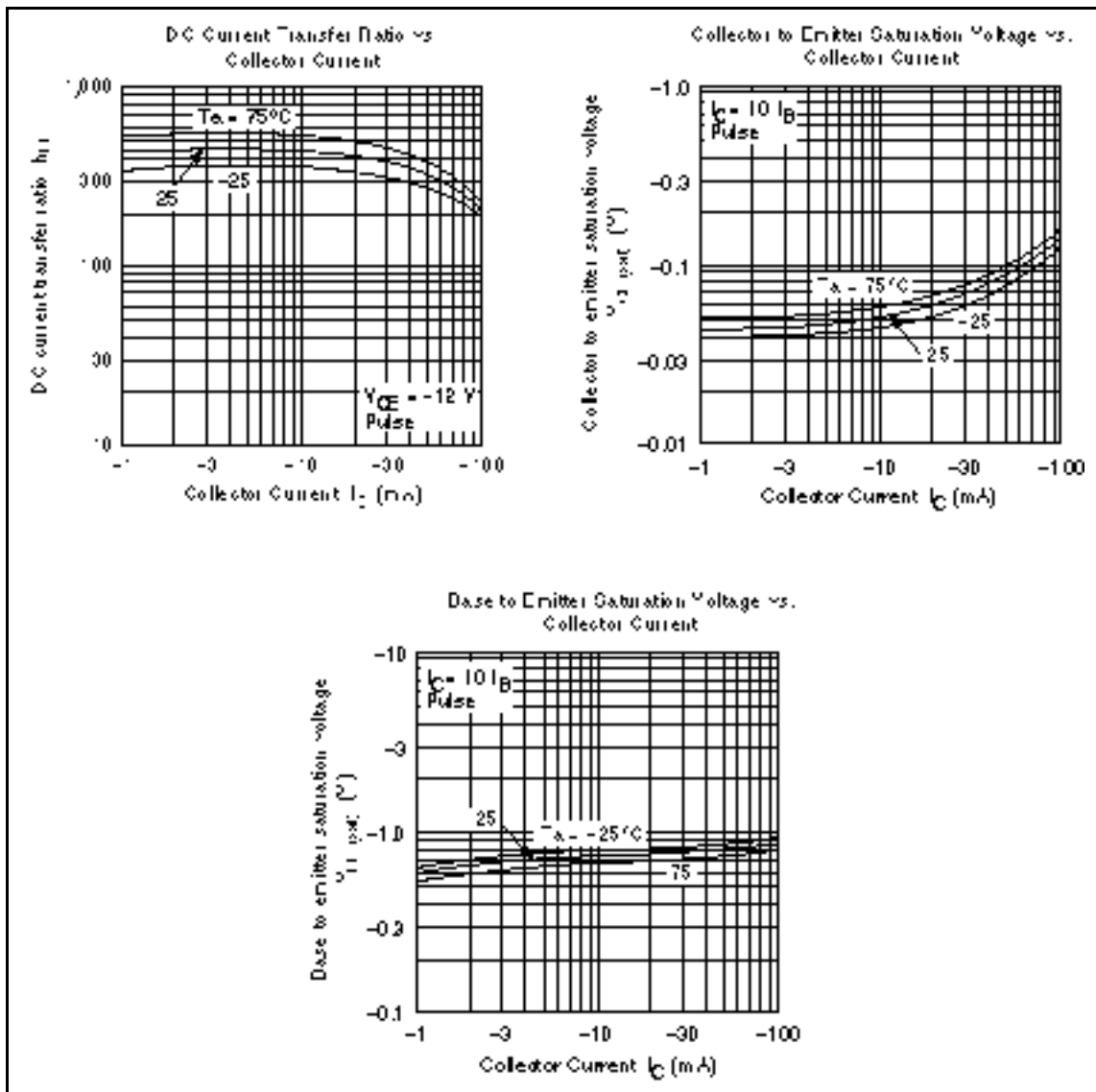
Notes: 1. The 2SA1484 is grouped by  $h_{FE}$  as follows.

2. Pulse test

Grade	D	E
Mark	IRD	IRE
$h_{FE}$	250 to 500	400 to 800







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# HITACHI

## **Hitachi, Ltd.**

Semiconductor & IC Div.  
Nippon Bldg., 2-5-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan  
Tel: Tokyo (03) 3270-2111  
Fax: (03) 3270-5109

For further information write to:

**Hitachi America, Ltd.**  
Semiconductor & IC Div.  
2000 Sierra Point Parkway  
Brisbane, CA 94005-4835  
U.S.A.  
Tel: 415-589-8300  
Fax: 415-589-4207

**Hitachi Europe GmbH**  
Electronic Components Group  
Continental Europe  
Dornacher StraÙe 3  
D-85622 Feldkirchen  
München  
Tel: 089-9 91 80-0  
Fax: 089-9 29 30 00

**Hitachi Europe Ltd.**  
Electronic Components Div.  
Northern Europe Headquarters  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 6YA  
United Kingdom  
Tel: 0628-885000  
Fax: 0628-778322

**Hitachi Asia Pte. Ltd.**  
45 Collyer Quay #20-00  
Hitachi Tower  
Singapore 0104  
Tel: 535-2100  
Fax: 535-1533

**Hitachi Asia (Hong Kong) Ltd.**  
Unit 705, North Tower,  
World Finance Centre  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon  
Hong Kong  
Tel: 27359218  
Fax: 27308074